

*MDS170L* 170 Watts, 36 Volts, Pulsed Avionics 1030/1090 MHz

<b>GENERAL DESCRIPTIO</b> The MDS170L is a high power COMMON designed for pulsed systems in the frequency transistor includes input and output premate device has gold thin-film metallization and highest MTTF. Low thermal resistance Sol junction temperature, extends life.	CASE OUTLINE 55KT, STYLE 1	
ABSOLUTE MAXIMUM	RATINGS	
Maximum Power Dissipation @ 25°C <sup>2</sup>	350 Watts	
Maximum Power Dissipation @ 25°C <sup>2</sup> Maximum Voltage and Current	350 Watts	
-	350 Watts 50 Volts	
Maximum Voltage and Current		
Maximum Voltage and Current BVces Collector to Base Voltage	50 Volts	
Maximum Voltage and CurrentBVcesCollector to Base VoltageBVeboEmitter to Base Voltage	50 Volts 3.5 Volts	
Maximum Voltage and CurrentBVcesCollector to Base VoltageBVeboEmitter to Base VoltageIcCollector Current	50 Volts 3.5 Volts	

## ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η <sub>c</sub> VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 1030 - 1090  MHz Vcc = 36 Volts PW = Note 1 DF = Note 1 F = 1030 MHz	170 7	40	34 10:1	Watts Watts dB %

Note 1: MODE- S Pulse Burst, 120  $\mu$ s at 50% Duty, Long term duty = 5%.

2: At rated pulse conditions

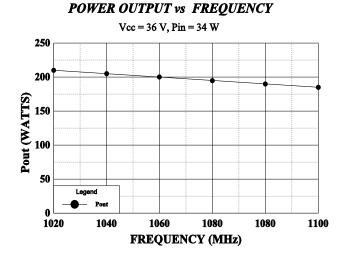
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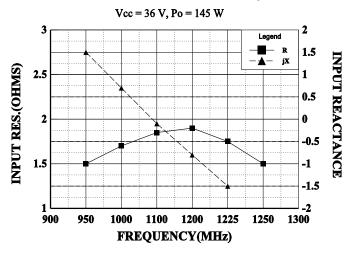
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## MDS170L



## SERIES INPUT IMPEDANCE vs FREQUENCY



Vcc = 36 V, Po = 145 W2 3 1.5 LOAD REACTANCE 2.5 1 LOAD RES.(OHMS) 0.5 Legend 2 0 ▲jХ -0.5 1.5 -1 -1.5 1 900 950 1000 1100 1200 1300 **FREQUENCY (MHz)** 



